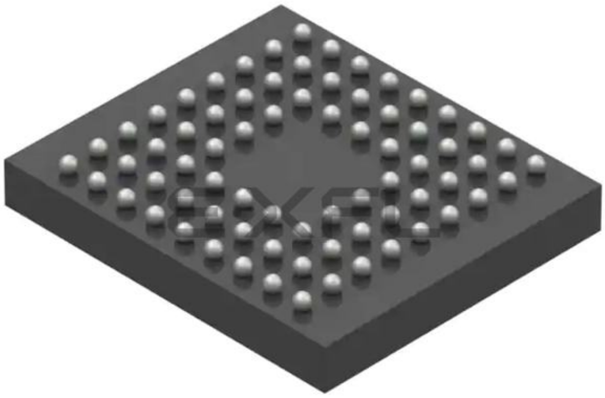

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	57
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	72-UFBGA, WLCSP
Supplier Device Package	72-WLCSP (4.41x3.76)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l486jgy6tr

List of tables

Table 2. STM32L486xx family device features and peripheral counts

Peripheral		STM32L486Zx	STM32L486Qx	STM32L486Vx	STM32L486Jx	STM32L486Rx
Flash memory		1 MB				
SRAM		128 KB				
External memory controller for static memories		Yes	Yes	Yes[1]	No	No
Quad SPI		Yes				
Timers	Advanced control	2 (16-bit)				
	General purpose	5 (16-bit) 2 (32-bit)				
	Basic	2 (16-bit)				
	Low power	2 (16-bit)				
	SysTick timer	1				
	Watchdog timers (independent, window)	2				
Comm. interfaces	SPI	3				
	I^2C	3				
	USART UART LPUART	3 2 1				
	SAI	2				
	CAN	1				
	USB OTG FS	Yes				
	SDMMC	Yes				
	SWPMI	Yes				
Digital filters for sigma-delta modulators		Yes (4 filters)				
Number of channels		8				
RTC		Yes				
Tamper pins		3			2	2
LCD COM x SEG		Yes 8x40 or 4x44	Yes 8x40 or 4x44	Yes 8x40 or 4x44	Yes 8x28 or 4x32	Yes 8x28 or 4x32
Random generator		Yes				
AES		Yes				

3.7 Boot modes

At startup, BOOT0 pin and BOOT1 option bit are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART, I2C, SPI, CAN and USB OTG FS in Device mode through DFU (device firmware upgrade).

3.8 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.9 Power supply management

3.9.1 Power supply schemes

- V_{DD} = 1.71 to 3.6 V: external power supply for I/Os (V_{DDIO1}), the internal regulator and the system analog such as reset, power management and internal clocks. It is provided externally through V_{DD} pins.
- V_{DDA} = 1.62 V (ADCs/COMPs) / 1.8 (DACs/OPAMPs) to 3.6 V: external analog power supply for ADCs, DACs, OPAMPs, Comparators and Voltage reference buffer. The V_{DDA} voltage level is independent from the V_{DD} voltage.
- V_{DDUSB} = 3.0 to 3.6 V: external independent power supply for USB transceivers. The V_{DDUSB} voltage level is independent from the V_{DD} voltage.
- V_{DDIO2} = 1.08 to 3.6 V: external power supply for 14 I/Os (PG[15:2]). The V_{DDIO2} voltage level is independent from the V_{DD} voltage.
- V_{LCD} = 2.5 to 3.6 V: the LCD controller can be powered either externally through VLCD pin, or internally from an internal voltage generated by the embedded step-up converter.
- V_{BAT} = 1.55 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Note: When the functions supplied by V_{DDA}, V_{DDUSB} or V_{DDIO2} are not used, these supplies should preferably be shorted to V_{DD}.

Note: If these supplies are tied to ground, the I/Os supplied by these power supplies are not 5 V tolerant (refer to Table 19: Voltage characteristics).

Note: V_{DDIOx} is the I/Os general purpose digital functions supply. V_{DDIOx} represents V_{DDIO1} or V_{DDIO2}, with V_{DDIO1} = V_{DD}. V_{DDIO2} supply voltage level is independent from V_{DDIO1}.

3.12 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. Fast I/O toggling can be achieved thanks to their mapping on the AHB2 bus.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

3.13 Direct memory access controller (DMA)

The device embeds 2 DMAs. Refer to *Table 7: DMA implementation* for the features implementation.

Direct memory access (DMA) is used in order to provide high-speed data transfer between peripherals and memory as well as memory to memory. Data can be quickly moved by DMA without any CPU actions. This keeps CPU resources free for other operations.

The two DMA controllers have 14 channels in total, each dedicated to managing memory access requests from one or more peripherals. Each has an arbiter for handling the priority between DMA requests.

The DMA supports:

- 14 independently configurable channels (requests)
- Each channel is connected to dedicated hardware DMA requests, software trigger is also supported on each channel. This configuration is done by software.
- Priorities between requests from channels of one DMA are software programmable (4 levels consisting of very high, high, medium, low) or hardware in case of equality (request 1 has priority over request 2, etc.)
- Independent source and destination transfer size (byte, half word, word), emulating packing and unpacking. Source/destination addresses must be aligned on the data size.
- Support for circular buffer management
- 3 event flags (DMA Half Transfer, DMA Transfer complete and DMA Transfer Error) logically ORed together in a single interrupt request for each channel
- Memory-to-memory transfer
- Peripheral-to-memory and memory-to-peripheral, and peripheral-to-peripheral transfers
- Access to Flash, SRAM, APB and AHB peripherals as source and destination
- Programmable number of data to be transferred: up to 65536.

Table 7. DMA implementation

DMA features	DMA1	DMA2
Number of regular channels	7	7

All comparators can wake up from Stop mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

3.19 Operational amplifier (OPAMP)

The STM32L486xx embeds two operational amplifiers with external or internal follower routing and PGA capability.

The operational amplifier features:

- Low input bias current
- Low offset voltage
- Low-power mode
- Rail-to-rail input

3.20 Touch sensing controller (TSC)

The touch sensing controller provides a simple solution for adding capacitive sensing functionality to any application. Capacitive sensing technology is able to detect finger presence near an electrode which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

The main features of the touch sensing controller are the following:

- Proven and robust surface charge transfer acquisition principle
- Supports up to 24 capacitive sensing channels
- Up to 3 capacitive sensing channels can be acquired in parallel offering a very good response time
- Spread spectrum feature to improve system robustness in noisy environments
- Full hardware management of the charge transfer acquisition sequence
- Programmable charge transfer frequency
- Programmable sampling capacitor I/O pin
- Programmable channel I/O pin
- Programmable max count value to avoid long acquisition when a channel is faulty
- Dedicated end of acquisition and max count error flags with interrupt capability
- One sampling capacitor for up to 3 capacitive sensing channels to reduce the system components
- Compatible with proximity, touchkey, linear and rotary touch sensor implementation
- Designed to operate with STMTouch touch sensing firmware library

Note: *The number of capacitive sensing channels is dependent on the size of the packages and subject to I/O availability.*

Table 13. SAI implementation

SAI features[1]	SAI1	SAI2
I2S, LSB or MSB-justified, PCM/DSP, TDM, AC’97	X	X
Mute mode	X	X
Stereo/Mono audio frame capability.	X	X
16 slots	X	X
Data size configurable: 8-, 10-, 16-, 20-, 24-, 32-bit	X	X
FIFO Size	X (8 Word)	X (8 Word)
SPDIF	X	X

1. X: supported

3.32 Single wire protocol master interface (SWPMI)

The Single wire protocol master interface (SWPMI) is the master interface corresponding to the Contactless Frontend (CLF) defined in the ETSI TS 102 613 technical specification. The main features are:

- full-duplex communication mode
- automatic SWP bus state management (active, suspend, resume)
- configurable bitrate up to 2 Mbit/s
- automatic SOF, EOF and CRC handling

SWPMI can be served by the DMA controller.

3.33 Controller area network (CAN)

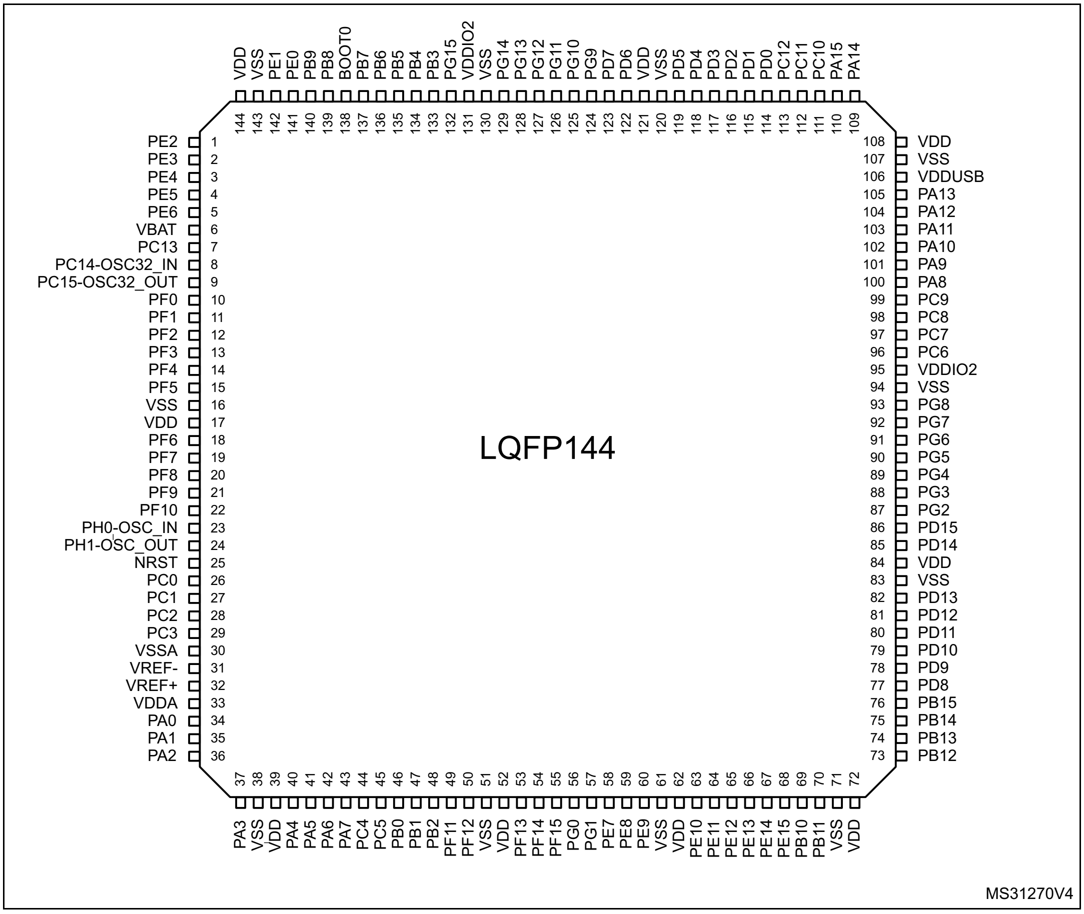
The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

The CAN peripheral supports:

- Supports CAN protocol version 2.0 A, B Active
- Bit rates up to 1 Mbit/s

4 Pinouts and pin description

Figure 5. STM32L486Zx LQFP144 pinout[1]



1. The above figure shows the package top view.

Table 15. STM32L486xx pin definitions

Pin Number					Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	**WLCSP72**	**LQFP100**	**UFBGA132**	**LQFP144**					**Alternate functions**	**Additional functions**
-	-	1	B2	1	PE2	I/O	FT_l	-	TRACECK, TIM3_ETR, TSC_G7_IO1, LCD_SEG38, FMC_A23, SAI1_MCLK_A, EVENTOUT	-
-	-	2	A1	2	PE3	I/O	FT_l	-	TRACED0, TIM3_CH1, TSC_G7_IO2, LCD_SEG39, FMC_A19, SAI1_SD_B, EVENTOUT	-
-	-	3	B1	3	PE4	I/O	FT	-	TRACED1, TIM3_CH2, DFSDM1_DATIN3, TSC_G7_IO3, FMC_A20, SAI1_FS_A, EVENTOUT	-
-	-	4	C2	4	PE5	I/O	FT	-	TRACED2, TIM3_CH3, DFSDM1_CKIN3, TSC_G7_IO4, FMC_A21, SAI1_SCK_A, EVENTOUT	-
-	-	5	D2	5	PE6	I/O	FT	-	TRACED3, TIM3_CH4, FMC_A22, SAI1_SD_A, EVENTOUT	RTC_TAMP3/ WKUP3
1	B9	6	E2	6	VBAT	S	-	-	-	-
2	B8	7	C1	7	PC13	I/O	FT	(1) (2)	EVENTOUT	RTC_TAMP1/ RTC_TS/ RTC_OUT/ WKUP2
3	C9	8	D1	8	PC14-OSC32_IN (PC14)	I/O	FT	(1) (2)	EVENTOUT	OSC32_IN
4	C8	9	E1	9	PC15-OSC32_OUT (PC15)	I/O	FT	(1) (2)	EVENTOUT	OSC32_OUT
-	-	-	D6	10	PF0	I/O	FT_f	-	I2C2_SDA, FMC_A0, EVENTOUT	-
-	-	-	D5	11	PF1	I/O	FT_f	-	I2C2_SCL, FMC_A1, EVENTOUT	-
-	-	-	D4	12	PF2	I/O	FT	-	I2C2_SMBA, FMC_A2, EVENTOUT	-
-	-	-	E4	13	PF3	I/O	FT_a	-	FMC_A3, EVENTOUT	ADC3_IN6
-	-	-	F3	14	PF4	I/O	FT_a	-	FMC_A4, EVENTOUT	ADC3_IN7
-	-	-	F4	15	PF5	I/O	FT_a	-	FMC_A5, EVENTOUT	ADC3_IN8

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see *Table 16*) (continued)

Port		**AF8**	**AF9**	**AF10**	**AF11**	**AF12**	**AF13**	**AF14**	**AF15**
		UART4, UART5, LPUART1	**CAN1, TSC**	**OTG_FS, QUADSPI**	**LCD**	**SDMMC1, COMP1, COMP2, FMC, SWPMI1**	**SAI1, SAI2**	**TIM2, TIM15, TIM16, TIM17, LPTIM2**	**EVENTOUT**
Port H	PH0	-	-	-	-	-	-	-	EVENTOUT
	PH1	-	-	-	-	-	-	-	EVENTOUT

Table 24. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions(1)	Min	Typ	Max	Unit
$t_{RSTTEMPO}$(2)	Reset temporization after BOR0 is detected	V_{DD} rising	-	250	400	µs
V_{BOR0}(2)	Brown-out reset threshold 0	Rising edge	1.62	1.66	1.7	V
		Falling edge	1.6	1.64	1.69	
V_{BOR1}	Brown-out reset threshold 1	Rising edge	2.06	2.1	2.14	V
		Falling edge	1.96	2	2.04	
V_{BOR2}	Brown-out reset threshold 2	Rising edge	2.26	2.31	2.35	V
		Falling edge	2.16	2.20	2.24	
V_{BOR3}	Brown-out reset threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{BOR4}	Brown-out reset threshold 4	Rising edge	2.85	2.90	2.95	V
		Falling edge	2.76	2.81	2.86	
V_{PVD0}	Programmable voltage detector threshold 0	Rising edge	2.1	2.15	2.19	V
		Falling edge	2	2.05	2.1	
V_{PVD1}	PVD threshold 1	Rising edge	2.26	2.31	2.36	V
		Falling edge	2.15	2.20	2.25	
V_{PVD2}	PVD threshold 2	Rising edge	2.41	2.46	2.51	V
		Falling edge	2.31	2.36	2.41	
V_{PVD3}	PVD threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{PVD4}	PVD threshold 4	Rising edge	2.69	2.74	2.79	V
		Falling edge	2.59	2.64	2.69	
V_{PVD5}	PVD threshold 5	Rising edge	2.85	2.91	2.96	V
		Falling edge	2.75	2.81	2.86	
V_{PVD6}	PVD threshold 6	Rising edge	2.92	2.98	3.04	V
		Falling edge	2.84	2.90	2.96	
V_{hyst_BORH0}	Hysteresis voltage of BORH0	Hysteresis in continuous mode	-	20	-	mV
		Hysteresis in other mode	-	30	-	
$V_{hyst\_BOR\_PVD}$	Hysteresis voltage of BORH (except BORH0) and PVD	-	-	100	-	mV
I_{DD} (BOR_PVD)(2)	BOR(3) (except BOR0) and PVD consumption from V_{DD}	-	-	1.1	1.6	µA
V_{PVM1}	V_{DDUSB} peripheral voltage monitoring	-	1.18	1.22	1.26	V

Table 35. Current consumption in Stop 1 mode

Symbol	Parameter	Conditions			TYP					MAX[1]					Unit
		-	-	V_{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD} (Stop 1)	Supply current in Stop 1 mode, RTC disabled	-	LCD disabled	1.8 V	6.59	24.7	92.7	208	437	16	62	232	520	1093	µA
				2.4 V	6.65	24.8	92.9	209	439	17	62	232	523	1098	
				3 V	6.65	24.9	93.3	210	442	17	62	233	525	1105	
				3.6 V	6.70	25.1	93.8	212	447	17	63	235	530	1118	
		-	LCD enabled[2] clocked by LSI	1.8 V	7.00	25.2	97.2	219	461	18	63	243	548	1153	
				2.4 V	7.14	25.4	97.5	220	463	18	64	244	550	1158	
				3 V	7.24	25.7	97.7	221	465	18	64	244	553	1163	
				3.6 V	7.36	26.1	98.7	223	471	18	65	247	558	1178	
I_{DD} (Stop 1 with RTC)	Supply current in stop 1 mode, RTC enabled	RTC clocked by LSI	LCD disabled	1.8 V	6.88	25.0	93.1	209	439	17	63	233	523	1098	µA
				2.4 V	7.02	25.2	93.7	210	441	18	63	234	525	1103	
				3 V	7.12	25.4	94.2	212	444	18	64	236	530	1110	
				3.6 V	7.25	25.7	95.2	214	449	18	64	238	535	1123	
			LCD enabled[2]	1.8 V	7.01	26.1	99.0	223	467	18	65	248	558	1168	
				2.4 V	7.14	26.3	99.6	225	470	18	66	249	563	1175	
				3 V	7.31	26.6	100.0	226	474	18	67	250	565	1185	
				3.6 V	7.41	26.9	102.0	229	480	19	67	255	573	1200	
		RTC clocked by LSE bypassed at 32768 Hz	LCD disabled	1.8 V	6.91	25.2	93.4	210	440	17	63	234	525	1100	
				2.4 V	7.04	25.3	94.2	211	443	18	63	236	528	1108	
				3 V	7.19	25.7	95.0	212	446	18	64	238	530	1115	
				3.6 V	7.97	26.0	96.1	215	451	20	65	240	538	1128	
		RTC clocked by LSE quartz[3] in low drive mode	LCD disabled	1.8 V	6.85	25.0	93.0	208.3	-	17	63	233	521	-	
				2.4 V	6.94	25.1	93.2	209.3	-	17	63	233	523	-	
				3 V	7.10	25.2	93.6	210.3	-	18	63	234	526	-	
				3.6 V	7.34	25.4	94.1	212.3	-	18	64	235	531	-	

Table 40. Peripheral current consumption (continued)

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
APB1	USART2 independent clock domain	4.1	3.6	3.8	µA/MHz
	USART2 APB clock domain	1.4	1.1	1.5	
	USART3 independent clock domain	4.7	4.1	4.2	
	USART3 APB clock domain	1.5	1.3	1.7	
	UART4 independent clock domain	3.9	3.2	3.5	
	UART4 APB clock domain	1.5	1.3	1.6	
	UART5 independent clock domain	3.9	3.2	3.5	
	UART5 APB clock domain	1.3	1.2	1.4	
	WWDG	0.5	0.5	0.5	
	All APB1 on	84.2	70.7	80.2	
APB2	AHB to APB2 bridge(4)	1.0	0.9	0.9	
	DFSDM1	5.6	4.6	5.3	
	FW	0.7	0.5	0.7	
	SAI1 independent clock domain	2.6	2.1	2.3	
	SAI1 APB clock domain	2.1	1.8	2.0	
	SAI2 independent clock domain	3.3	2.7	3.0	
	SAI2 APB clock domain	2.4	2.1	2.2	
	SDMMC1 independent clock domain	4.7	3.9	4.2	
	SDMMC1 APB clock domain	2.5	1.9	2.1	
	SPI1	2.0	1.6	1.9	
	SYSCFG/VREFBUF/COMP	0.6	0.4	0.5	
	TIM1	8.3	6.9	7.9	
	TIM8	8.6	7.1	8.1	
	TIM15	4.1	3.4	3.9	
	TIM16	3.0	2.5	2.9	
	TIM17	3.0	2.4	2.9	
	USART1 independent clock domain	4.9	4.0	4.4	
	USART1 APB clock domain	1.5	1.3	1.7	
	All APB2 on	56.8	43.3	48.2	
ALL		256.8	189.6	215.5	

Table 61. I/O AC characteristics(1)(2)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	5	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	10	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1.5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	52	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	140	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	17	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	37	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	10	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	50	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	15	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	9	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	16	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	40	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	4.5	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	9	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	21	

Table 72. VREFBUF characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DDA}(VREF BUF)	VREFBUF consumption from V_{DDA}	I_{load} = 0 µA	-	16	25	µA
		I_{load} = 500 µA	-	18	30	
		I_{load} = 4 mA	-	35	50	

1. Guaranteed by design, unless otherwise specified.
2. In degraded mode, the voltage reference buffer can not maintain accurately the output voltage which will follow (V_{DDA} - drop voltage).
3. Guaranteed by test in production.
4. The capacitive load must include a 100 nF capacitor in order to cut-off the high frequency noise.
5. To correctly control the VREFBUF inrush current during start-up phase and scaling change, the V_{DDA} voltage should be in the range [2.4 V to 3.6 V] and [2.8 V to 3.6 V] respectively for V_{RS} = 0 and V_{RS} = 1.

6.3.22 Temperature sensor characteristics

Table 75. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{TS} linearity with temperature	-	±1	±2	°C
Avg_Slope(2)	Average slope	2.3	2.5	2.7	mV/°C
V_{30}	Voltage at 30°C (±5 °C)(3)	0.742	0.76	0.785	V
t_{START} (TS_BUF)(1)	Sensor Buffer Start-up time in continuous mode(4)	-	8	15	µs
t_{START}(1)	Start-up time when entering in continuous mode(4)	-	70	120	µs
t_{S_temp}(1)	ADC sampling time when reading the temperature	5	-	-	µs
I_{DD}(TS)(1)	Temperature sensor consumption from V_{DD}, when selected by ADC	-	4.7	7	µA

1. Guaranteed by design.
2. Guaranteed by characterization results.
3. Measured at V_{DDA} = 3.0 V ±10 mV. The V_{30} ADC conversion result is stored in the TS_CAL1 byte. Refer to *Table 8: Temperature sensor calibration values*.
4. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

6.3.23 V_{BAT} monitoring characteristics

Table 76. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	39	-	kΩ
Q	Ratio on V_{BAT} measurement	-	3	-	-
Er(1)	Error on Q	-10	-	10	%
t_{S_vbat}(1)	ADC sampling time when reading the VBAT	12	-	-	µs

1. Guaranteed by design.

Table 77. V_{BAT} charging characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{BC}	Battery charging resistor	VBRS = 0	-	5	-	kΩ
		VBRS = 1	-	1.5	-	

Table 88. SD / MMC dynamic characteristics, V_{DD}=2.7 V to 3.6 V[1] (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CMD, D outputs (referenced to CK) in SD default mode						
t_{OVD}	Output valid default time SD	f_{PP} = 50 MHz	-	4.5	5	ns
t_{OHD}	Output hold default time SD	f_{PP} = 50 MHz	0	-	-	ns

1. Guaranteed by characterization results.

Table 89. eMMC dynamic characteristics, V_{DD} = 1.71 V to 1.9 V[1][2]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/f_{PCLK2} frequency ratio	-	-	-	4/3	-
$t_{W(CKL)}$	Clock low time	f_{PP} = 50 MHz	8	10	-	ns
$t_{W(CKH)}$	Clock high time	f_{PP} = 50 MHz	8	10	-	ns
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	f_{PP} = 50 MHz	0	-	-	ns
t_{IH}	Input hold time HS	f_{PP} = 50 MHz	5	-	-	ns
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	f_{PP} = 50 MHz	-	13.5	15.5	ns
t_{OH}	Output hold time HS	f_{PP} = 50 MHz	9	-	-	ns

1. Guaranteed by characterization results.
2. C_{LOAD} = 20pF.

Figure 35. SDIO high-speed mode

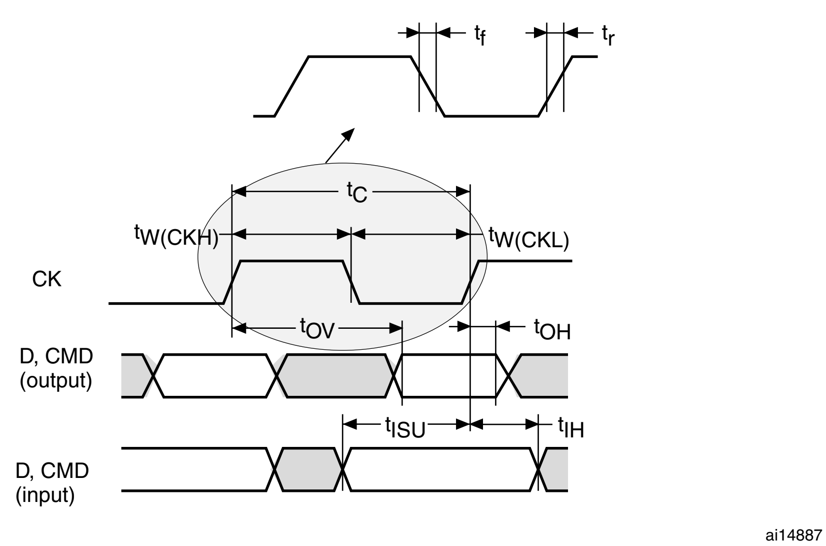


Table 95. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}$-0.5	$3T_{HCLK}$+2	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK}$-0.5	$2T_{HCLK}$+0.5	
$t_{w(NOE)}$	FMC_NOE low time	T_{HCLK}+0.5	T_{HCLK}+1	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	3	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	1	
$t_{w(NADV)}$	FMC_NADV low time	T_{HCLK}-0.5	T_{HCLK}+1	
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high	0	-	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	T_{HCLK}-0.5	-	
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	T_{HCLK}-2	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	T_{HCLK}-1	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

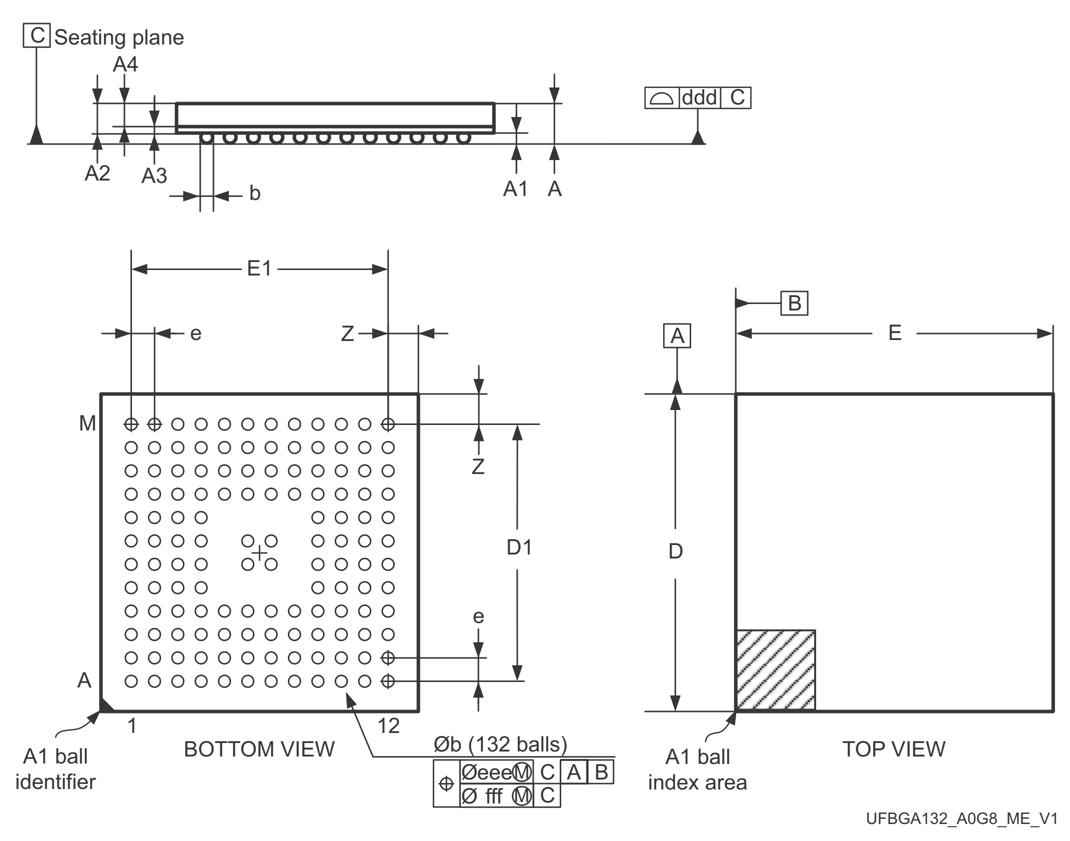
Table 96. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}$+2	$8T_{HCLK}$+4	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}$-1	$5T_{HCLK}$+1.5	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}$+1.5	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}$+1	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

7.2 UFBGA132 package information

Figure 52. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 107. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data

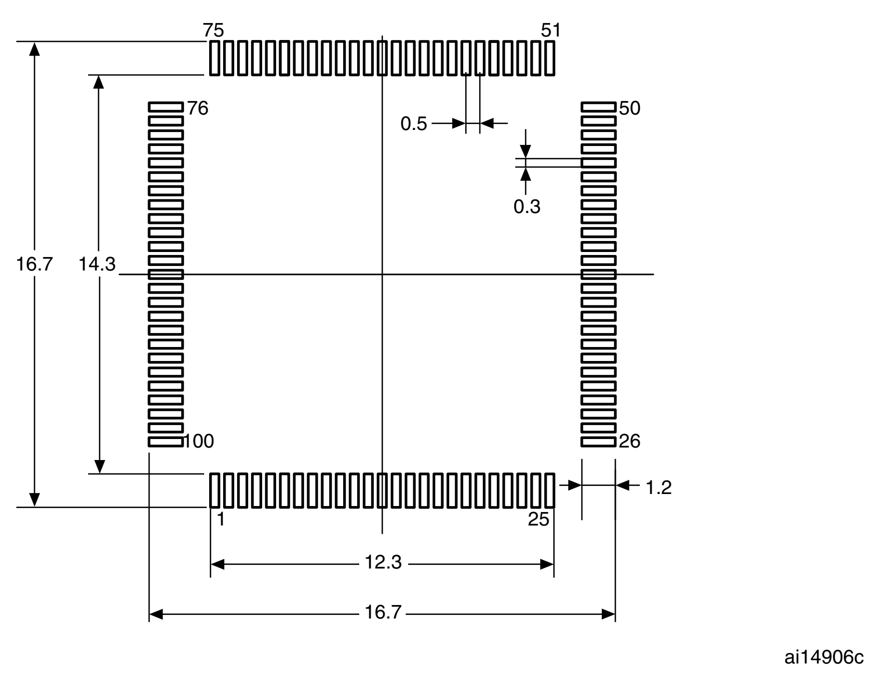
Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	0.0094
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
E	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-

Table 109. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 56. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint



1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.